

Magnetic domain structure of micro-patterned PtMn/NiFe exchange bias bilayers

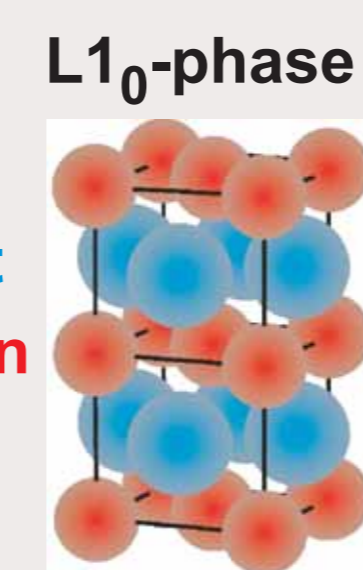
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Motivation

- Magnetic behavior determined by**
 - Exchange coupling
 - Magnetic anisotropies
 - Curie temperature
 - Magnetic damping
 - Structural origins**
 - Interface morphology
 - Structural phases (chemically ordered)
 - Composition
- Ion irradiation and implantation changes structure or composition and thereby magnetic properties
- Non-topographic magnetic patterning**
 - Exchange coupling between irradiated (implanted) and virgin areas
 - Magnetic features are determined by micromagnetism only
 - Patterning below the intrinsic micromagnetic feature size leads to artificial magnetic materials with new adjustable properties
 - Topographic magnetic patterning**
 - Magnetic features are determined by topography and micromagnetism

Exchange Bias System Ni₈₀Fe₂₀/Pt₅₀Mn₅₀

- PtMn – antiferromagnetic only in chemically ordered L₁₀-phase**
 - Very sensitive on structural changes (ion irradiation)
- High exchange bias field** → technologically relevant
- Magnetic sensor applications**



Experimental techniques

- Sample Preparation**
 - Ion beam and physical vapor deposition
 - Focused Ga irradiation (magnetic patterning)
- Magnetic characterization**

Integral:

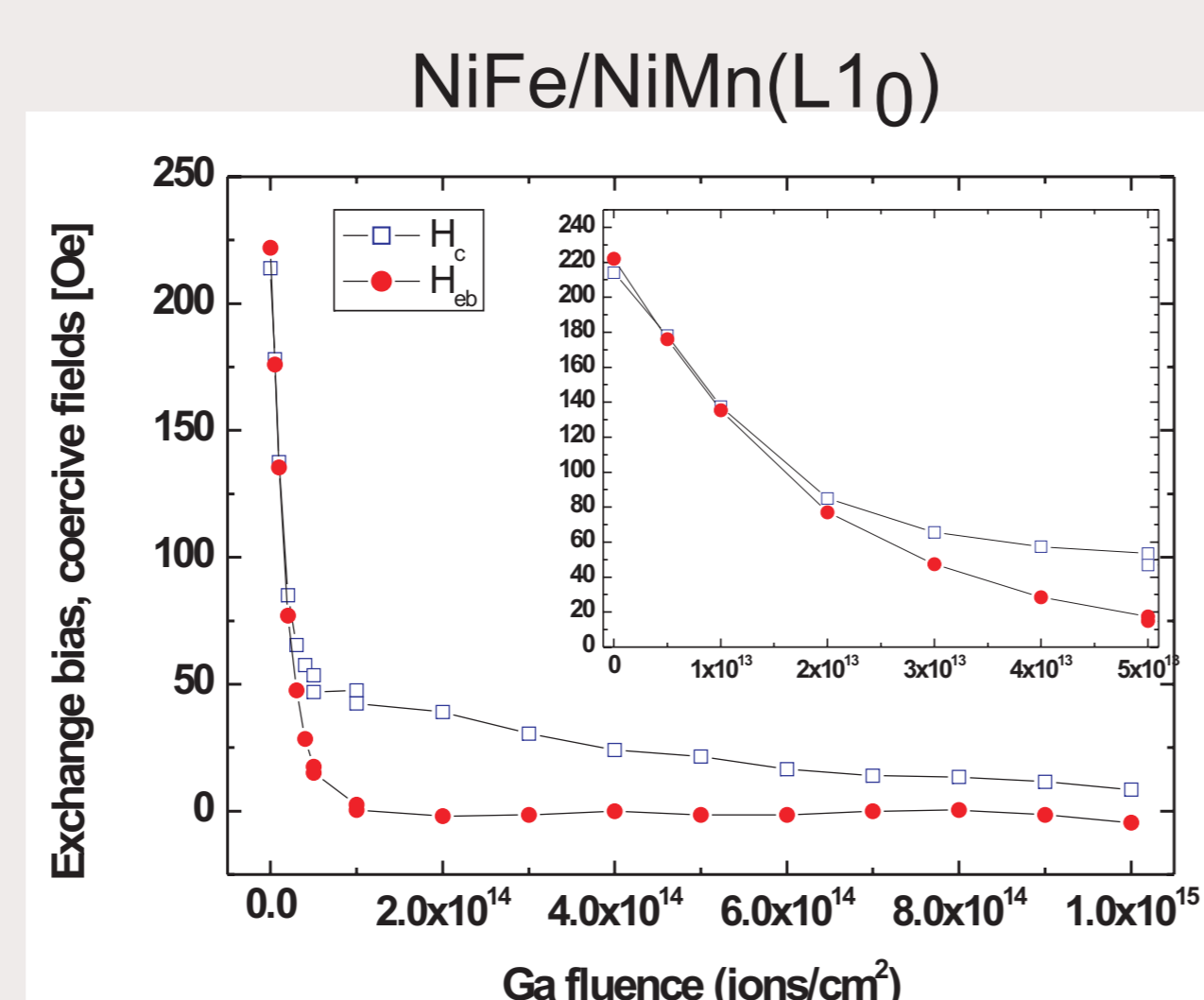
 - Magneto-optic Kerr magnetometry (MOKE)
 - Vibrating sample magnetometry (VSM)

Spatially resolved:

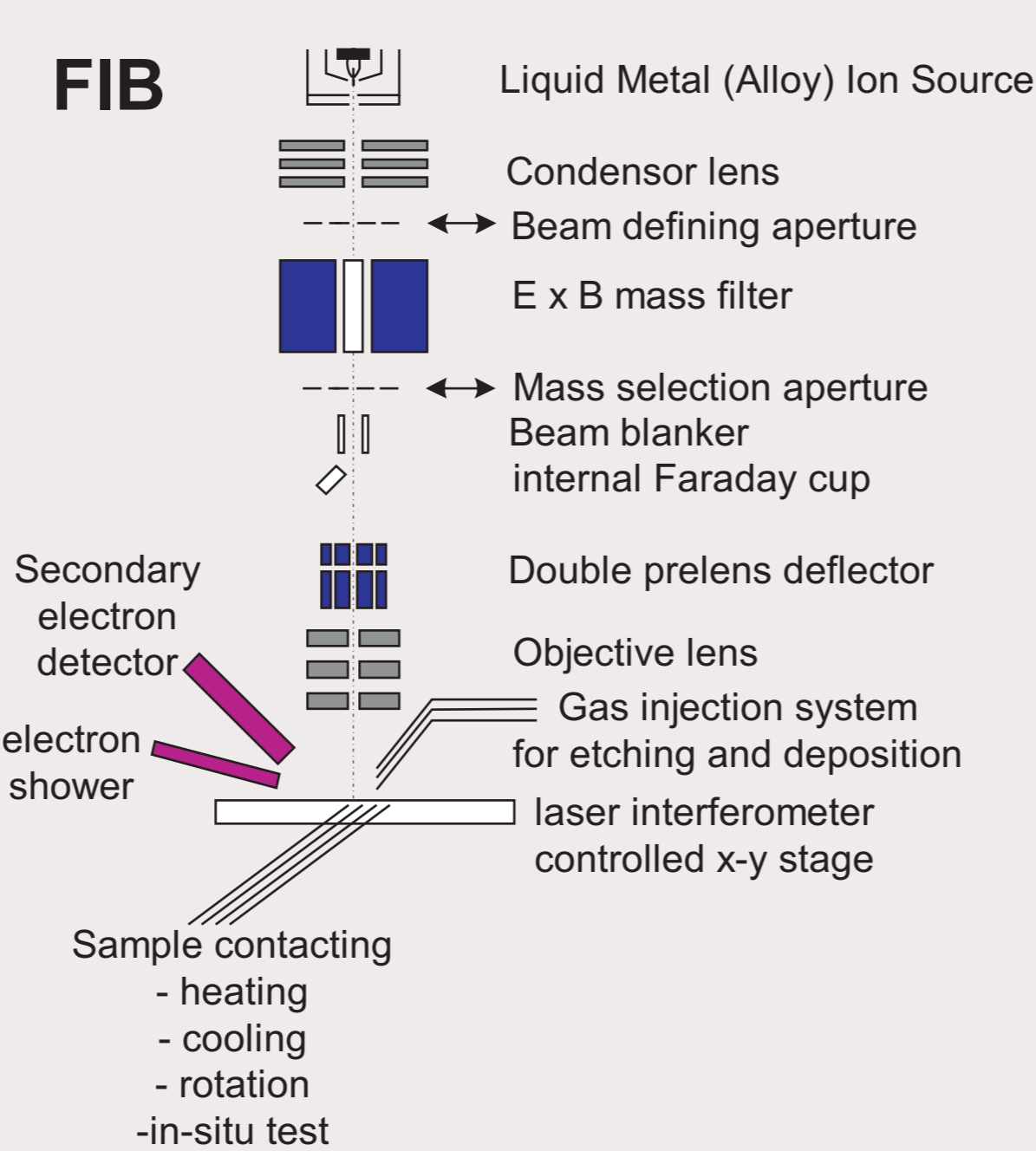
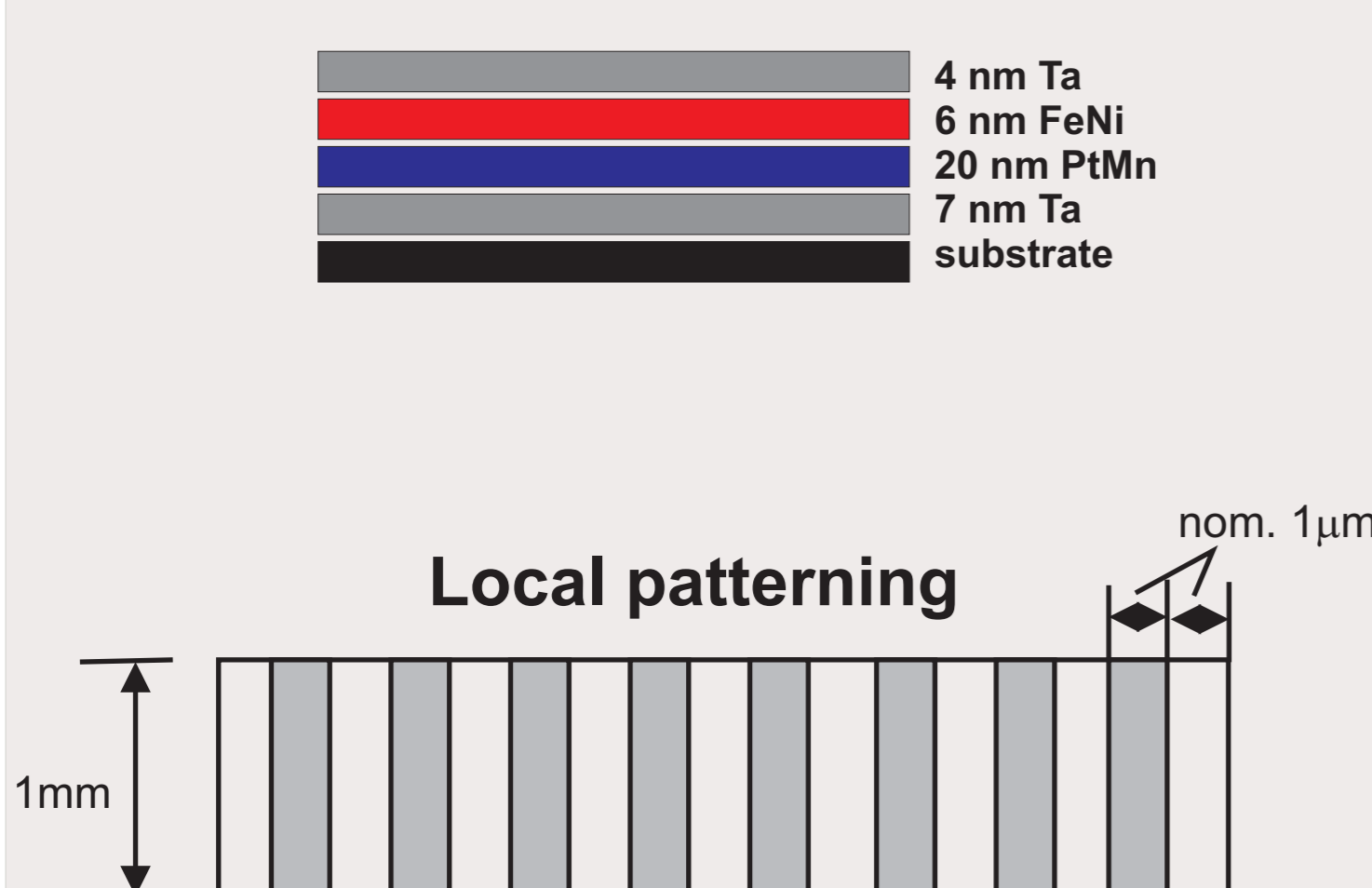
 - Wide-field Kerr microscopy
 - Magnetic force microscopy (MFM)

Ion fluence dependence

- 25 keV Ga irradiation with focused ion beam
- Fluence dependence investigated for Ni₅₀Mn₅₀ which is comparable to Pt₅₀Mn₅₀
- 1×10¹⁴ Ga/cm² are sufficient to suppress exchange bias completely

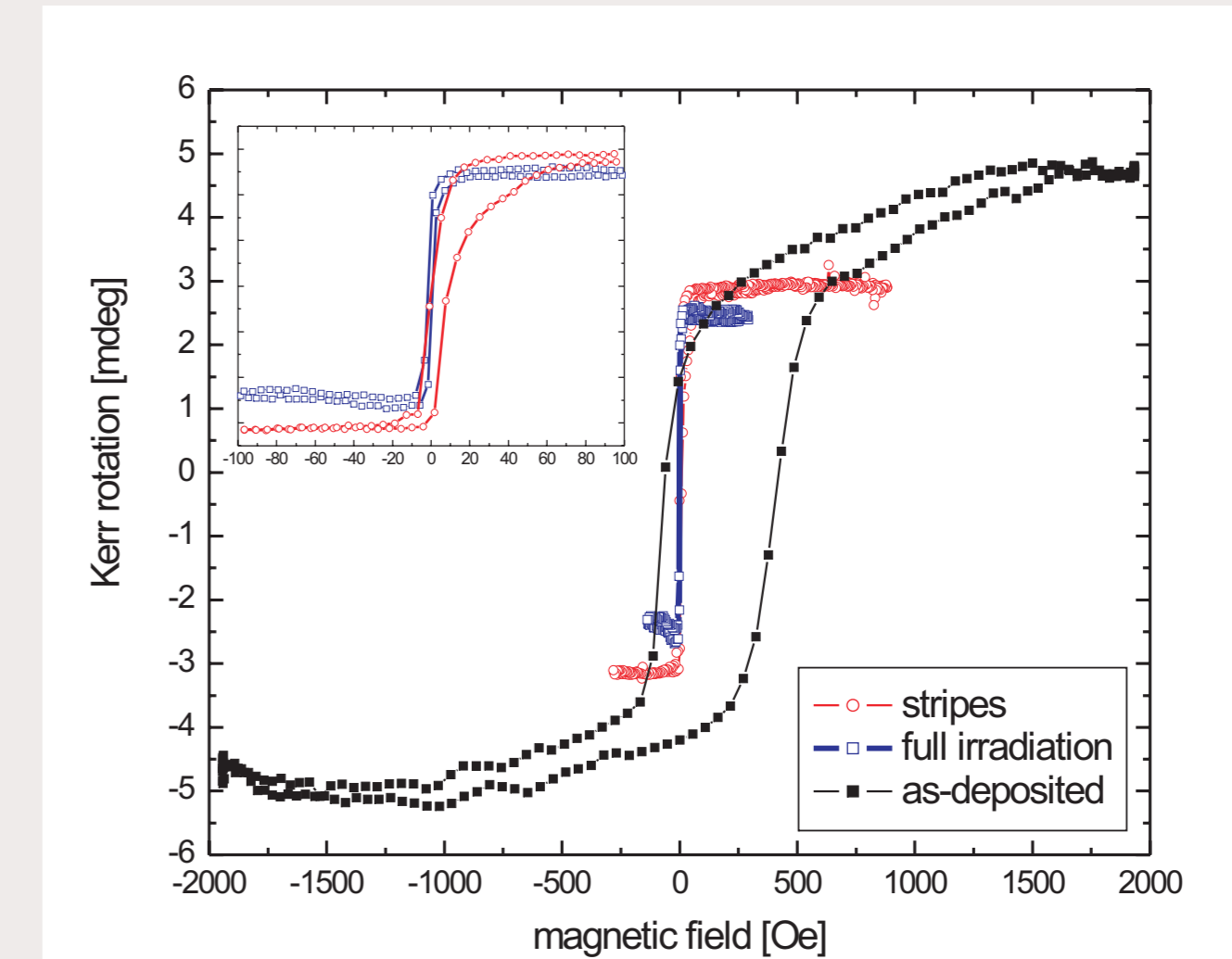
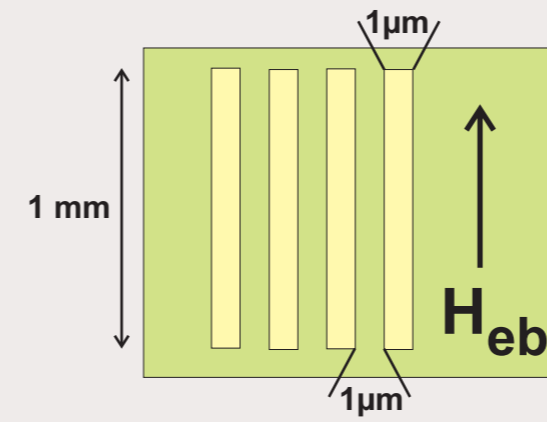


Sample structure



Magnetization reversal

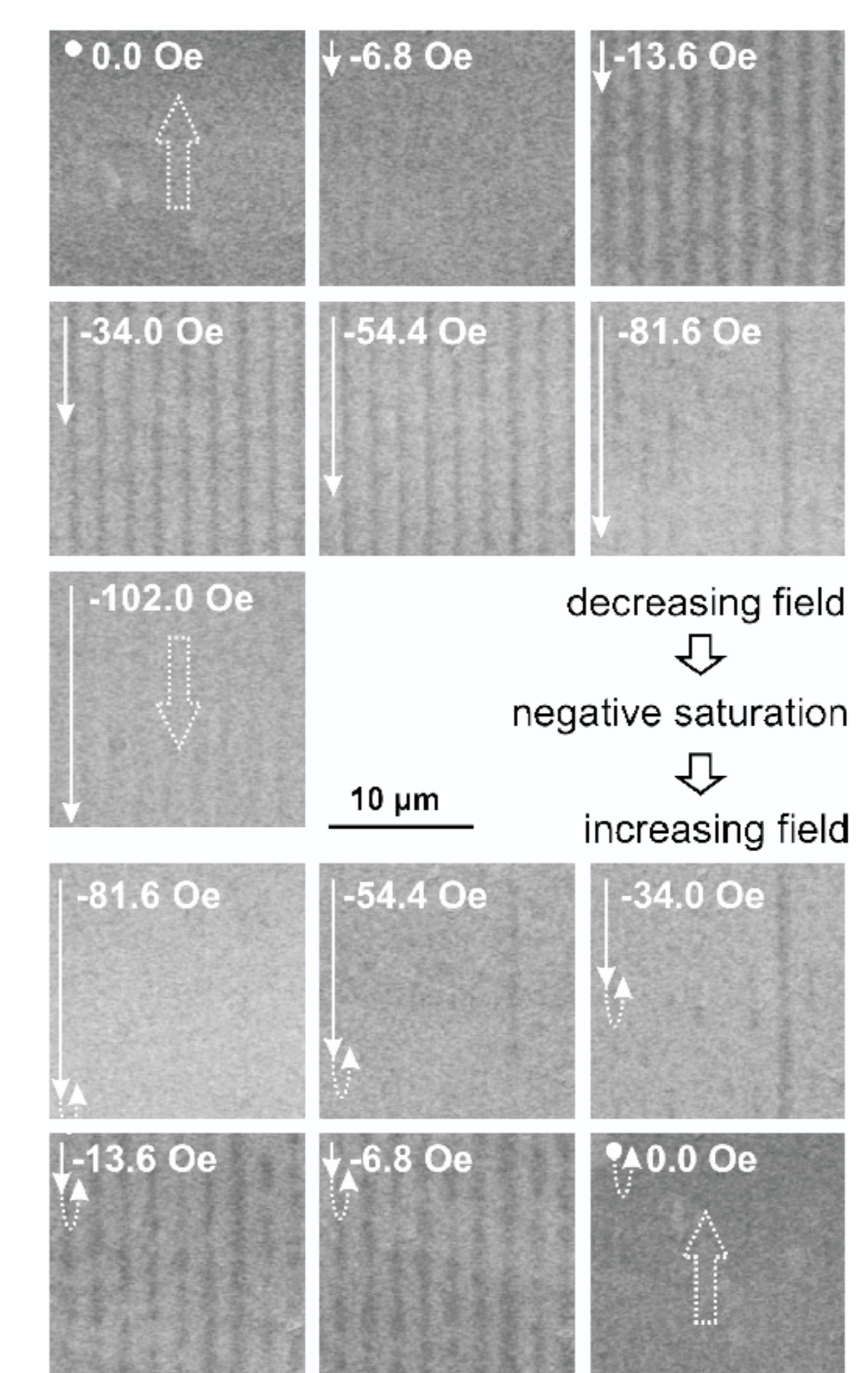
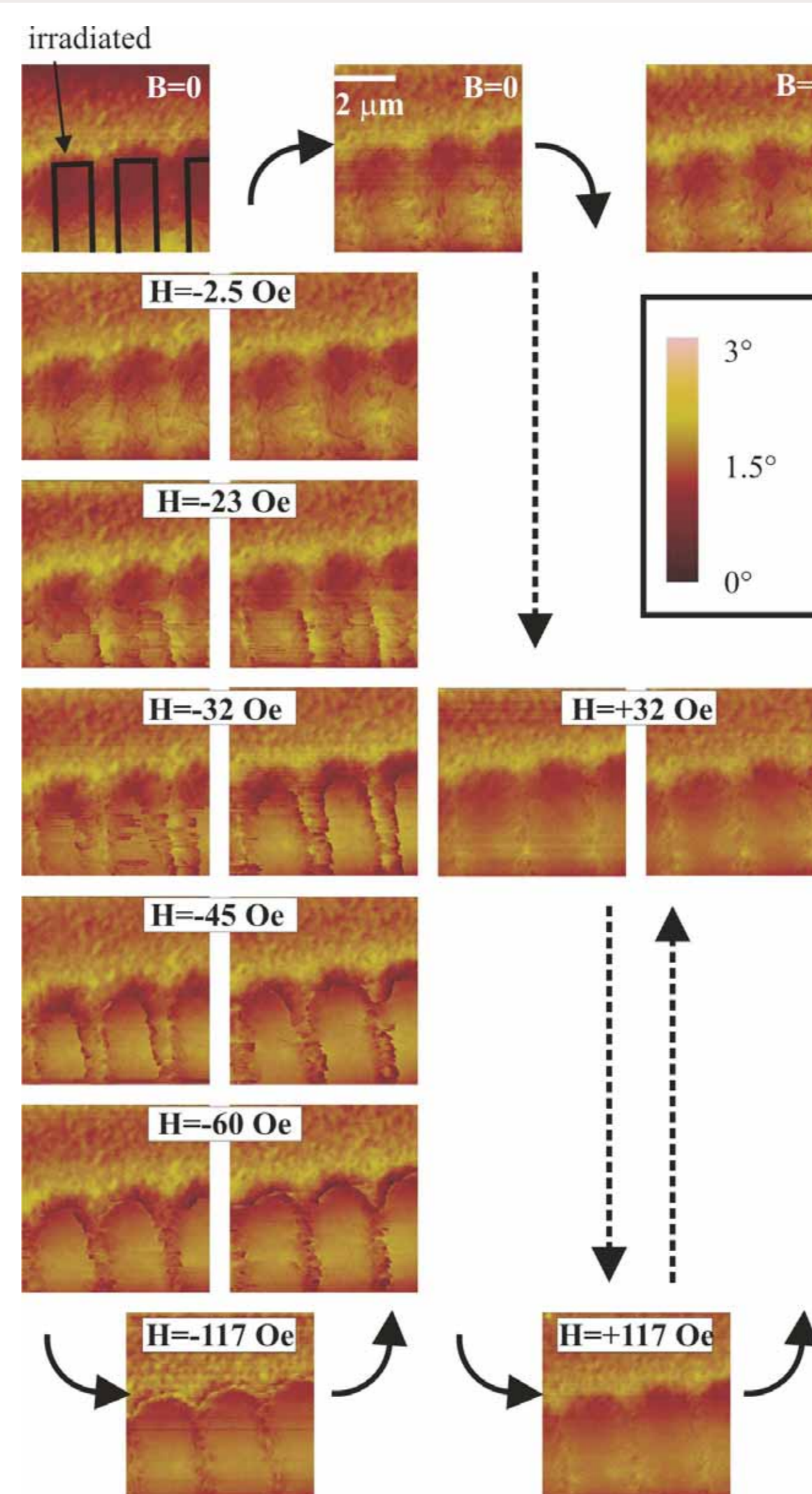
- As-deposited: $H_{eb} = 180$ Oe
- Full area irradiation (1×10^{14} Ga/cm²): $H_{eb} = 0$ Oe consistent with fluence dependence
- Stripe array: $H_{eb} \approx 30$ Oe
strong interaction between irradiated and non-irradiated areas



Magnetic patterning

Magnetic force microscopy

Kerr microscopy



- Kerr microscopy**
 - Decreasing field branch: antiparallel orientation of irradiated stripes and surrounding area between $H = -13$ and $H = -60$ Oe.
 - Increasing field branch: antiparallel orientation between $H = -15$ and $H = -5$ Oe
- Magnetic force microscopy**
 - Between $H = -12$ Oe and $H = -80$ Oe sharp Neél walls between irradiated stripes and surrounding area observed
 - For increasing negative fields successive increase in domain size of the irradiated area at the expense of the non-irradiated area
 - At $H = -100$ Oe – magnetization in non-irradiated areas between the stripes is completely reversed due to magnetic interactions
 - Magnetization ripple as a remainder of the non-irradiated areas persists up to large field values consistent with large exchange bias field value of the unpatterned film

Summary

- Magnetic patterning by local ion irradiation**
 - L₁₀-phase (NiMn, PtMn) very sensitive on ion irradiation
 - Interactions between irradiated and non-irradiated areas
 - Reduced exchange bias field
 - Switching field influenced by the magnetization reversal in the surrounding area
 - Domain size is a function of applied field → complicated magnetization reversal behavior

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